



UDT1605

Preliminary

NPN EPITAXIAL SILICON TRANSISTOR

120V NPN SILICON HIGH VOLTAGE DARLINGTON TRANSISTOR

DESCRIPTION

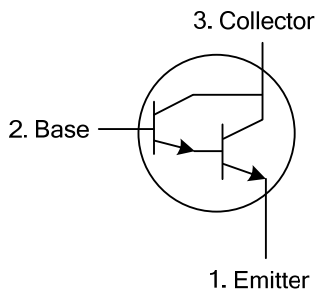
The UTC **UDT1605** is an NPN Darlington transistor. Utilizing UTC's advanced technology, **UDT1605** features ultra-high DC current gain and low collector-emitter saturation voltage, making it suitable for efficient driving functions.

The UTC **UDT1605** is suitable for a variety of efficient driving functions, etc.

FEATURES

- * High breakdown voltage
- * Low saturation voltage
- * Ultra-high DC current gain

SYMBOL



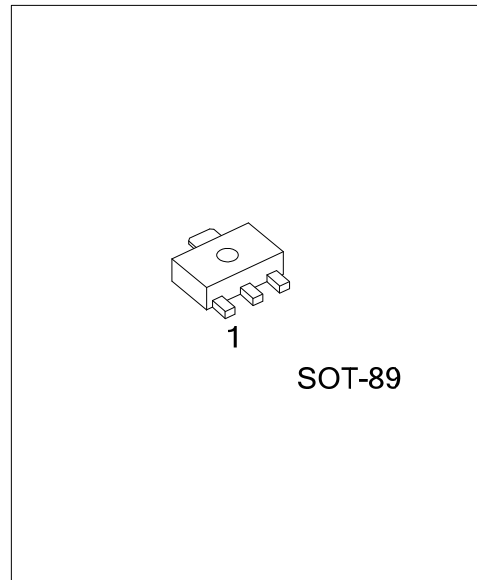
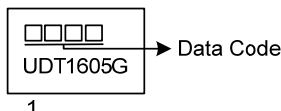
ORDERING INFORMATION

| Ordering Number | Package | Pin Assignment | | | Packing |
|-----------------|---------|----------------|---|---|-----------|
| | | 1 | 2 | 3 | |
| UDT1605G-AB3-R | SOT-89 | B | C | E | Tape Reel |

Note: Pin Assignment: E: Emitter B: Base C: Collector

| | |
|---|--|
| <p>UDT1605G-AB3-R</p> <ul style="list-style-type: none"> (1) Packing Type (2) Package Type (3) Green Package | <ul style="list-style-type: none"> (1) R: Tape Reel (2) AB3: SOT-89 (3) G: Halogen Free and Lead Free |
|---|--|

MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$, unless otherwise stated)

| PARAMETER | SYMBOL | RATINGS | UNIT |
|--|-----------|----------|----------------------|
| Collector-Base Voltage | V_{CBO} | 140 | V |
| Collector-Emitter Voltage | V_{CEO} | 120 | V |
| Emitter-Base Voltage | V_{EBO} | 10 | V |
| Peak Pulse Current | I_{CM} | 4 | A |
| Continuous Collector Current | I_C | 1 | A |
| Power Dissipation at $T_A=25^\circ\text{C}$ (Note 1) | P_D | 1 | W |
| Linear Derating Factor | | 8 | mW/ $^\circ\text{C}$ |
| Power Dissipation at $T_A=25^\circ\text{C}$ (Note 2) | P_D | 2.8 | W |
| Linear Derating Factor | | 22 | mW/ $^\circ\text{C}$ |
| Junction Temperature | T_J | -55~+150 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{STG} | -55~+150 | $^\circ\text{C}$ |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

| PARAMETER | SYMBOL | RATINGS | UNIT |
|------------------------------|-----------------|---------|---------------------------|
| Junction to Ambient (Note 1) | $R_{\theta JA}$ | 125 | $^\circ\text{C}/\text{W}$ |
| Junction to Ambient (Note 2) | $R_{\theta JA}$ | 45 | $^\circ\text{C}/\text{W}$ |

Notes: 1. For a device surface mounted on 25mmx25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

2. For a device surface mounted on FR4 PCB measured at $t \leq 5$ secs.

■ ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$, unless otherwise stated)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--------------------------------------|---------------|--|-----|------|-----|---------------|
| Collector-Base Breakdown Voltage | BV_{CBO} | $I_C=100\mu\text{A}$ | 140 | | | V |
| Collector-Emitter Breakdown Voltage | BV_{CEO} | $I_C=10\text{mA}$ (Note) | 120 | | | V |
| Emitter-Base Breakdown Voltage | BV_{EBO} | $I_E=100\mu\text{A}$ | 10 | | | V |
| Collector Cut-Off Current | I_{CBO} | $V_{CB}=10\text{V}$ | | | 100 | nA |
| | | $V_{CB}=120\text{V}$, $T_{AMB}=100^\circ\text{C}$ | | | 10 | μA |
| Emitter Cut-Off Current | I_{EBO} | $V_{EB}=8\text{V}$ | | | 0.1 | μA |
| Collector Emitter Cut-Off Current | I_{CES} | $V_{CES}=120\text{V}$ | | | 10 | μA |
| Collector-Emitter Saturation Voltage | $V_{CE(SAT)}$ | $I_C=250\text{mA}$, $I_B=0.25\text{mA}$ (Note) | | | 1 | V |
| | | $I_C=1\text{A}$, $I_B=1\text{mA}$ (Note) | | | 1.5 | V |
| Base-Emitter Saturation Voltage | $V_{BE(SAT)}$ | $I_C=1\text{A}$, $I_B=1\text{mA}$ (Note) | | | 1.8 | V |
| Base-Emitter Turn-On Voltage | $V_{BE(ON)}$ | $I_C=1\text{A}$, $V_{CE}=5\text{V}$ (Note) | | | 1.7 | V |
| DC Current Gain | h_{FE} | $I_C=50\text{mA}$, $V_{CE}=5\text{V}$ (Note) | 2K | | | |
| | | $I_C=500\text{mA}$, $V_{CE}=5\text{V}$ (Note) | 5K | | | |
| | | $I_C=1\text{A}$, $V_{CE}=5\text{V}$ (Note) | 2K | 100K | | |
| | | $I_C=2\text{A}$, $V_{CE}=5\text{V}$ (Note) | 0.5 | | | |
| Transition Frequency | f_T | $I_C=100\text{mA}$, $V_{CE}=10\text{V}$, $f=20\text{MHz}$ | 150 | | | MHz |
| Input Capacitance | C_{IBO} | $V_{CB}=500\text{mV}$, $f=1\text{MHz}$ | | 90 | | pF |
| Output Capacitance | C_{OBO} | $V_{CB}=10\text{V}$, $f=1\text{MHz}$ | | 15 | | pF |
| Turn-On Time | $t_{(ON)}$ | $I_C=500\text{mA}$, $V_{CE}=10\text{V}$ $I_{B1}=I_{B2}=0.5\text{mA}$ | | 0.5 | | μs |
| Turn-Off Time | $t_{(OFF)}$ | $I_C=500\text{mA}$, $V_{CE}=10\text{V}$ $I_{B1}=I_{B2}=0.5\text{mA}$ | | 1.6 | | μs |

Note: Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

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